

Solid State Relay OCMOS FET

PS7241-AT1, PS7241-AT5

PHOTO TRANSISTOR AND MOS FET OUTPUT TYPE 8-PIN SOP 400 V BREAK DOWN VOLTAGE 2-ch Optical Coupled MOS FET

DESCRIPTION

The PS7241-AT1 and PS7241-AT5 are solid state relays containing GaAs LEDs on the light emitting side (input side) and MOS FETs (+ Photo transistor) on the output side.

They are suitable for analog signal control because of their low offset and high linearity.

FEATURES

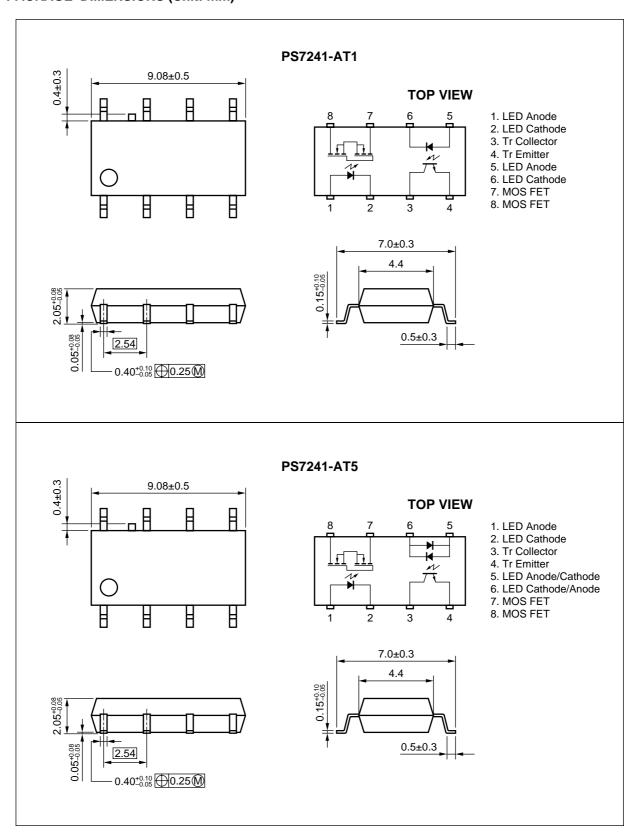
- 2 channel type (OCMOS FET + Photocoupler)
- Low LED operating current (IF = 2 mA)
- · Designed for AC/DC switching line changer
- Small and thin package (8-pin SOP, Height = 2.1 mm)
- Low offset voltage
- Ordering number of taping product: PS7241-AT1-F3, F4, PS7241-AT5-F3, F4
- · Safety standards
 - UL approved: File No. E72422 (S)
 - BSI approved: No. 8190/8191
 - CSA approved: No. CA 101391

APPLICATIONS

- Exchange equipment
- Measurement equipment
- · FA/OA equipment

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PACKAGE DIMENSIONS (Unit: mm)



ORDERING INFORMATION

Part Number	Package	Packing Style	Application Part Number 1
PS7241-AT1	8-pin SOP	Magazine case 45 pcs	PS7241-AT1
PS7241-AT1-F3		Embossed Tape 1 500 pcs/reel	
PS7241-AT1-F4			
PS7241-AT5		Magazine case 45 pcs	PS7241-AT5
PS7241-AT5-F3		Embossed Tape 1 500 pcs/reel	
PS7241-AT5-F4			

^{*1} For the application of the Safety Standard, following part number should be used.

ABSOLUTE MAXIMUM RATINGS (TA = 25°C, unless otherwise specified)

Parameter			Symbol	Ratings	Unit
OCMOS FET Diode Forward Current (DC)		Forward Current (DC)	lF	50	mA
		Reverse Voltage	VR	5.0	V
		Power Dissipation	Po	50	mW/ch
		Peak Forward Current 1	IFP	1	Α
	MOS FET	Break Down Voltage	VL	400	V
		Continuous Load Current	lι	120	mA
		Pulse Load Current ² (AC/DC Connection)	ILP	250	mA
		Power Dissipation	Po	430	mW
Photocoupler	Diode	Forward Current	lF	50	mA
		Reverse Voltage ^{*3}	VR	5.0	V
		Power Dissipation	PD	50	mW/ch
		Peak Forward Current 1	IFP	1	Α
	Transistor	Collector to Emitter Voltage	Vceo	40	V
		Emitter to Collector Voltage	VECO	6	V
		Collector Current	Ic	80	mA
		Power Dissipation	Pc	100	mW
Isolation Voltage '4			BV	1 500	Vr.m.s.
Total Power Dissipation			Рт	630	mW
Operating Ambient Temperature			TA	-40 to +80	°C
Storage Temperature			Tstg	-40 to +100	°C

^{*1} PW = 100 μ s, Duty Cycle = 1%

^{*2} PW = 100 ms, 1 shot

^{*3} PS7241-AT1 only

^{*4} AC voltage for 1 minute at $T_A = 25$ °C, RH = 60% between input and output

RECOMMENDED OPERATING CONDITIONS (TA = 25°C)

Parameter		Symbol	MIN.	TYP.	MAX.	Unit
OCMOS FET	LED Operating Current	lF	2	10	20	mA
	LED Off Voltage	VF	0		0.5	V

ELECTRICAL CHARACTERISTICS (TA = 25°C)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
OCMOS	Diode	Forward Voltage	VF	IF = 10 mA		1.2	1.4	V
FET		Reverse Current	lR	V _R = 5 V			5.0	μΑ
	MOS FET	Off-state Leakage Current	Loff	V _D = 400 V		0.03	1.0	μΑ
		Output Capacitance	Cout	V _D = 0 V, f = 1 MHz		65		pF
	Coupler	LED On-state Current	IFon	IL = 120 mA			2.0	mA
		On-state Resistance	R _{on1}	IF = 10 mA, IL = 10 mA		20	30	Ω
			Ron2	$I_F = 10 \text{ mA}, I_L = 120 \text{ mA}, t \le 10 \text{ ms}$			25	
		Turn-on Time ^{*1}	ton	IF = 10 mA, Vo = 5 V,		0.3	1.0	ms
		Turn-off Time [™]	t off	$PW \geq 10 \text{ ms, } R_L = 500 \ \Omega$		0.04	0.2	
		Isolation Resistance	R _{I-O}	Vi-o = 1.0 kVpc	10°			Ω
		Isolation Capacitance	C _{I-O}	V = 0 V, f = 1 MHz		1.1		pF
Photo-	Diode	Forward Voltage	VF	IF = 10 mA		1.2	1.4	V
coupler		Reverse Current ²	lR	V _R = 5 V			5.0	μΑ
	Transistor	Collector to Emitter Dark Current	ICEO	Vce = 40 V, I _F = 0 mA			100	nA
		Collector to Emitter Breakdown Voltage	BVceo	Ic = 1 mA	40			V
		Emitter to Collector Breakdown Voltage	BVECO	Iε = 100 μA	6			V
	Coupler	Current Transfer Ratio	CTR	IF = 5 mA, VcE = 5 V	50		400	%
		Collector Saturation Voltage	VCE (sat)	IF = 10 mA, Ic = 2 mA			0.3	V
		Isolation Resistance	R _{I-O}	Vi-o = 1.0 kVpc	10 ¹¹			Ω
		Isolation Capacitance	C _{I-O}	V = 0 V, f = 1 MHz		0.4		pF
		Rise Time	tr	Vcc = 5 V, Ic = 2 mA,		3.0		μs
		Fall Time	tr	R _L = 100 Ω		5.0		

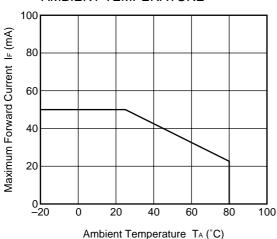
^{*1} The turn-on time and turn-off time are specified as input-pulse width ≥ 10 ms.
Be aware that when the device operates with an input-pulse width of under 10 ms, the turn-on time and turn-off time will increase.

*

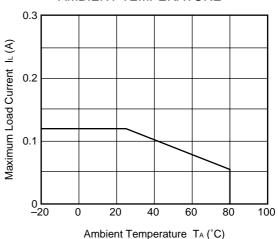
^{*2} PS7241-AT1 only

OCMOS TYPICAL CHARACTERISTICS (TA = 25°C, unless otherwise specified)

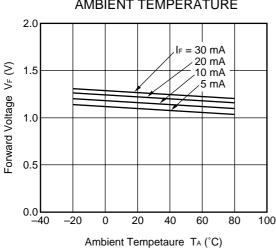




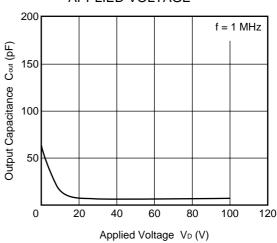
MAXIMUM LOAD CURRENT vs. AMBIENT TEMPERATURE



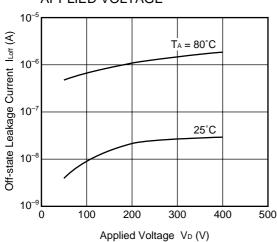
FORWARD VOLTAGE vs. AMBIENT TEMPERATURE



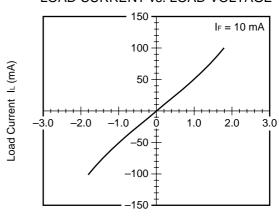
OUTPUT CAPACITANCE vs. APPLIED VOLTAGE



OFF-STATE LEAKAGE CURRENT vs. APPLIED VOLTAGE

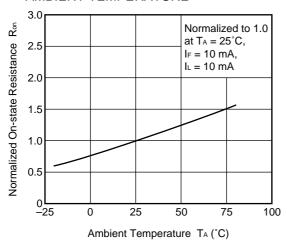


LOAD CURRENT vs. LOAD VOLTAGE

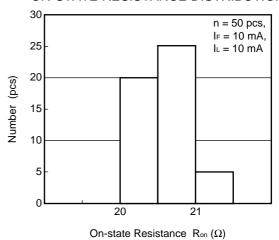


Load Voltage V_L (V)

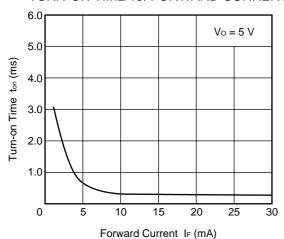
NORMALIZED ON-STATE RESISTANCE vs. AMBIENT TEMPERATURE



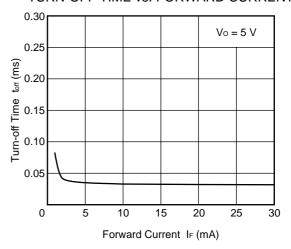
ON-STATE RESISTANCE DISTRIBUTION



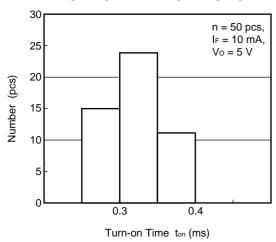
TURN-ON TIME vs. FORWARD CURRENT



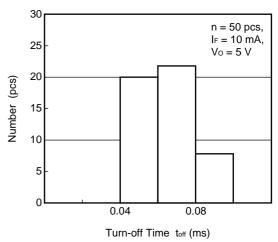
TURN-OFF TIME vs. FORWARD CURRENT



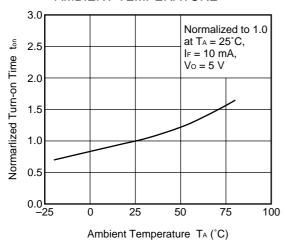
TURN-ON TIME DISTRIBUTION



TURN-OFF TIME DISTRIBUTION

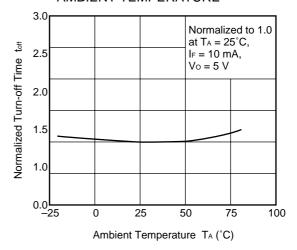


NORMALIZED TURN-ON TIME vs. AMBIENT TEMPERATURE



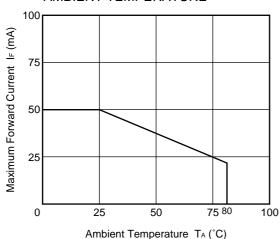
Remark The graphs indicate nominal characteristics.

NORMALIZED TURN-OFF TIME vs. AMBIENT TEMPERATURE

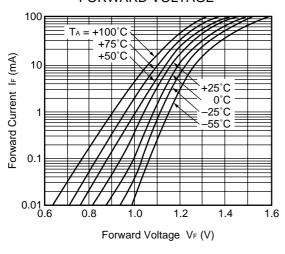


PHOTOCOUPLER TYPICAL CHARACTERISTICS (TA = 25°C, unless otherwise specified)

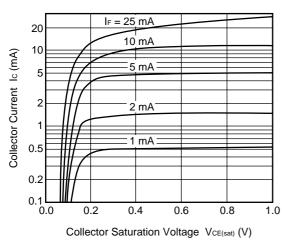
MAXIMUM FORWARD CURRENT vs. AMBIENT TEMPERATURE



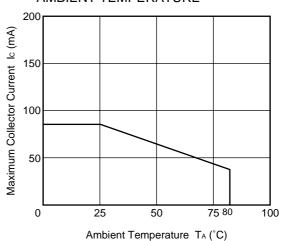
FORWARD CURRENT vs. FORWARD VOLTAGE



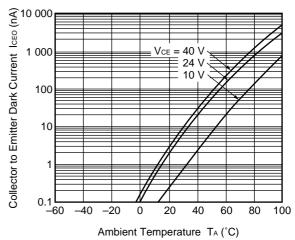
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



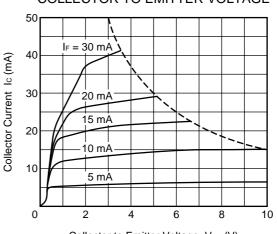
MUXIMUM COLLECTOR CURRENT vs. AMBIENT TEMPERATURE



COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE

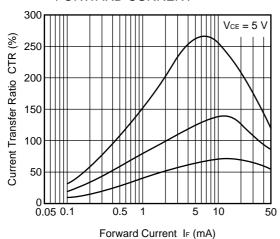


COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

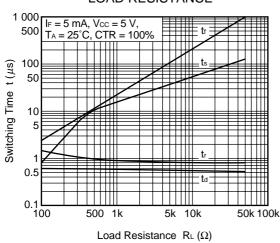


Collector to Emitter Voltage VcE (V)

CURRENT TRANSFER RATIO vs. FORWARD CURRENT

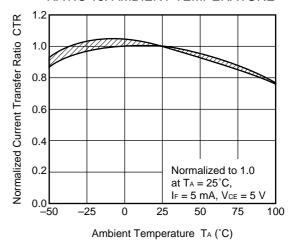


SWITCHING TIME vs. LOAD RESISTANCE

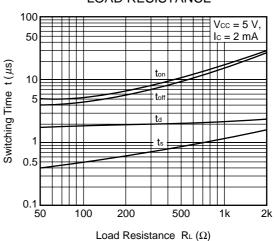


Remark The graphs indicate nominal characteristics.

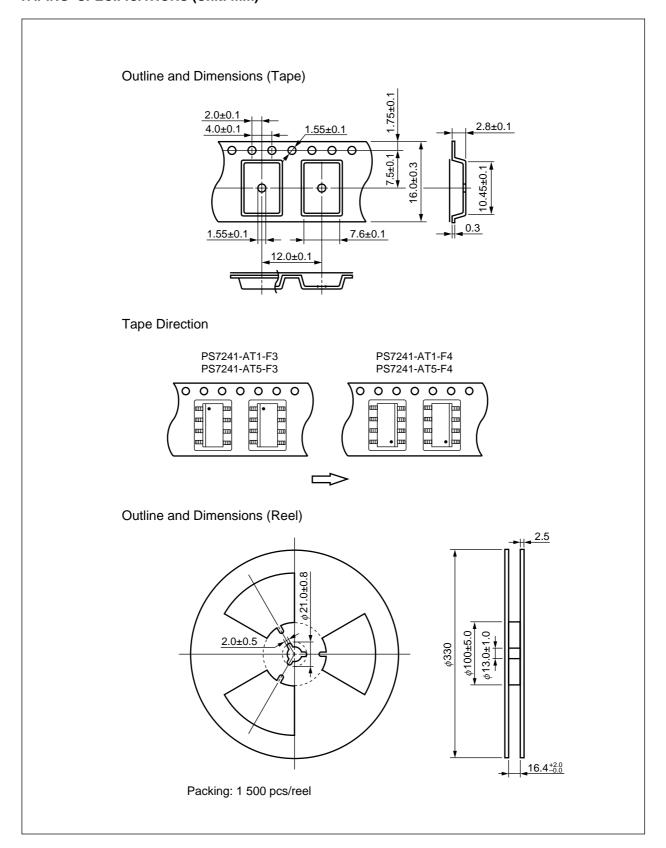
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



SWITCHING TIME vs. LOAD RESISTANCE



TAPING SPECIFICATIONS (Unit: mm)



RECOMMENDED SOLDERING CONDITIONS

(1) Infrared reflow soldering

Peak reflow temperature
 235°C (package surface temperature)

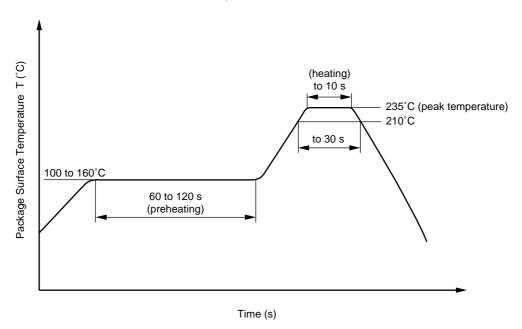
• Time of temperature higher than 210°C 30 seconds or less

• Number of reflows Two

Flux
 Rosin flux containing small amount of chlorine (The flux with a

maximum chlorine content of 0.2 Wt % is recommended.)

Recommended Temperature Profile of Infrared Reflow



(2) Dip soldering

• Temperature 260°C or below (molten solder temperature)

• Time 10 seconds or less

• Number of times One

• Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of

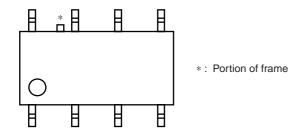
0.2 Wt % is recommended.)

(3) Cautions

Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

Avoid shorting between portion of frame and leads.



SAFETY INFORMATION ON THIS PRODUCT

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GaAs Products

The product contains gallium arsenide, GaAs.

GaAs vapor and powder are hazardous to human health if inhaled or ingested.

- Do not destroy or burn the product.
- Do not cut or cleave off any part of the product.
- · Do not crush or chemically dissolve the product.
- · Do not put the product in the mouth.

Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.

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M8E 00.4